



G. Device & Process Modeling, Simulation and Reliability 분과

2019년 2월 14일(목), 11:00-12:30

Room B (마루홀, 2층)

[TB2-G] Modeling & Simulation I : Reliability

좌장: 홍성민 교수(GIST), 유현용 교수(고려대학교)

<p>TB2-G-1 11:00-11:15</p>	<p>The Effects of Fluorine Implantation on Device Parameters and Reliability in a 110-nm Dual Gate Oxide CMOS Technology Meng Li, Seunghyun Han, Dongseok Kim, Yongjin Jeon, Jeongho Shin, Namjo Lee, Sunha Hwang, Myunghee Nam, Jeongsoo Park, and Inwook Cho <i>TD Office 2, R&D Center, SK Hynix System IC</i></p>
<p>TB2-G-2 11:15-11:30</p>	<p>Improved Electrical Characteristics and Reliability of p-MOSFET with Gate Fluorine Implant Seonhaeng Lee, Keon Yoo, Youngmi Ryu, Yuri Choi, Kibong Nam, Seunghun Son, and Seonyong Cha <i>SK Hynix</i></p>
<p>TB2-G-3 11:30-11:45</p>	<p>Development of Time-Dependent-Dielectric Breakdown Analysis Solution Kiron Park, Suhyun Kim, Sookyung Park, and Jongwook Jeon <i>Department of Electrical and Electronic Engineering, Konkuk University</i></p>
<p>TB2-G-4 11:45-12:00</p>	<p>Analysis of Hot Carrier Degradation in Short Channel MOSFET according to Temperature Jongsu Kim^{1,2}, Myounggon Kang³, Jongwook Jeon⁴, and Hyungcheol Shin^{1,2} ¹<i>Inter-University Semiconductor Research Center, Seoul National University,</i> ²<i>School of Electrical Engineering and Computer Science, Seoul National University,</i> ³<i>Department of Electronics Engineering, Korea National University of Transportation,</i> ⁴<i>Department of Electronics Engineering, Konkuk University</i></p>
<p>TB2-G-5 12:00-12:15</p>	<p>Bias Temperature Stress Instability of Multi-Layered MoS₂ Field Effect Transistors with CYTOP Passivation Seung Gi Seo, Hyeong Cheol Park, Dhananjay Mishra, and Sung Hun Jin <i>Department of Electronic Engineering, Incheon National University</i></p>
<p>TB2-G-6 12:15-12:30</p>	<p>Drain Avalanche Hot Carrier (DAHC) for Channel Junction Analysis of Tunnel FETs Donghwan Lim¹, Hoonhee Han¹, Soo Cheol Kang², Byoung Hun Lee², and Changhwan Choi¹ ¹<i>Division and Materials Science and Engineering, Hanyang University,</i> ²<i>School of Material Science and Engineering, Gwangju Institute of Science and Technology</i></p>